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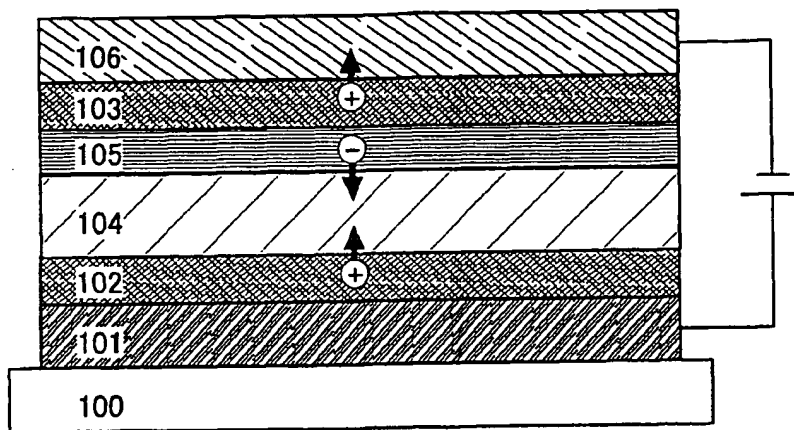
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(54) Title: LIGHT EMITTING ELEMENT



(57) Abstract: It is an object of the present invention to provide a light-emitting element having a structure in which the drive voltage is relatively low. Further, it is an object of the invention to provide a highly reliable light emitting device by alleviating the stress to the light emitting layer. Further, it is another object of the invention to provide a light emitting element having a structure in which increase in the drive voltage over time is small. It is an object of the present invention to provide a display device in which the drive voltage is low and increase in the drive voltage over time is small and which can withstand long-term use. In a light emitting element, a layer in contact with an electrode serves as a hole generating layer such as an organic compound layer containing a P-type semiconductor or an electron accepting material, a light emitting layer is provided between hole generating layers, an electron generating layer is formed between the hole generation layer on the cathode side and the light emitting layer.